



2CK120

SILICON EPITAXIAL PLANAR SWITCHING DIODE

REVERSE VOLTAGE: 75V

FORWARD CURRENT: 150mA

**TECHNICAL
SPECIFICATION**

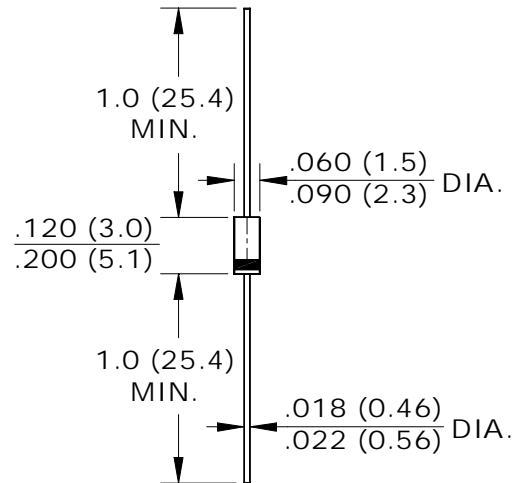
FEATURES

- Small glass structure ensures high reliability
- Fast switching
- Low leakage
- High temperature soldering guaranteed:
250°C/10S/9.5mm lead length
at 5 lbs tension

MECHANICAL DATA

- Terminal: Plated axial leads solderable per
MIL-STD 202E, method 208C
- Case: Glass, hermetically sealed
- Polarity: Color band denotes cathode
- Mounting position: Any

DO - 35



Dimensions in inches and (millimeters)

MAXIMUM RATINGS AND CHARACTERISTICS

(Ratings at 25°C ambient temperature unless otherwise specified)

RATINGS	SYMBOL	VALUE	UNITS
Reverse Voltage	V_R	75	V
Peak Reverse Voltage	V_{RM}	100	V
Forward Current (average)	I_O	150	mA
Repetitive Forward Peak Current	I_{FRM}	400	mA
Forward Voltage ($I_F=10mA$)	V_F	1	V
Reverse Current ($V_R=20V$)	I_{R1}	25	nA
Reverse Current ($V_R=75V$)		5	μA
Reverse Current ($V_R=20V, T_J=100^\circ C$)	I_{R2}	50	μA
Capacitance (note 1)	C_t	4	pF
Reverse Charge ($I_F=10mA$)	Q_r	57	pC
Thermal Resistance (junction to ambient, note 2)	$R_{\theta(ja)}$	0.35	$^\circ C/mW$
Operating Junction and Storage Temperature Range	T_{STG}, T_J	-55~+175	$^\circ C$

Notes:

1. $V_R=0V, f=1 MHz$
2. Valid provided that leads are kept at ambient temperature at a distance of 8mm from case.